



### Rev.02 - 21 November 2022

**Product data sheet** 

#### **1. General description**

Hyperfast power diode in a 2-lead TO220 plastic package.



## 2. Features and benefits

- Excellent avalanche energy robustness
- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

Symbol	Parameter	Conditions	Notes	s Values			Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage				650		V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30		A	
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 109 °C; square-wave pulse		60			A
FSM non-repetitive peak forward current		t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; <u>Fig. 4</u>		270			A
		$t_{\text{p}}$ = 8.3 ms; $T_{j(\text{init})}$ = 25 °C; sine-wave pulse			297		А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>		-	20	-	ns

# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode	$\int \int \int dx$	
2	А	anode	Γ Υ	K <u>– K</u> – A 001aaa020
mb	mb	mounting base; connected to cathod		

# 6. Ordering information

Table 3. Ordering information								
Type number	Package	Orderable part number	Packing	Small packing	Package	Package		
	name		method	quantity	version	issue date		
BYC30M-650P	TO220-2L	BYC30M-650PQ	Tube	50	TO220d-2L	13-Oct-2022		

## 7. Marking

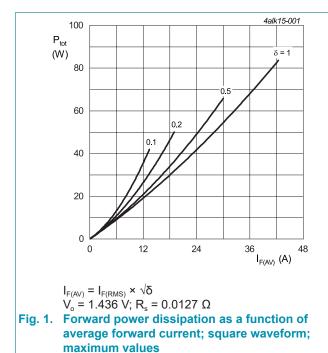
Table 4. Marking codes	
Type number	Marking codes
BYC30M-650P	BYC30M 650P

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			650	V
V <sub>RWM</sub>	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 109 °C; Fig. 1; Fig. 2; Fig. 3		30	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 109 °C; square-wave pulse		60	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		270	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		297	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
Tj	junction temperature			-65 to 175	°C



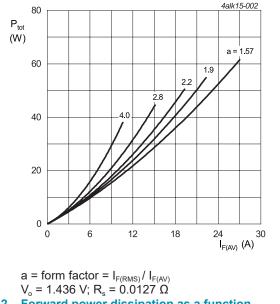
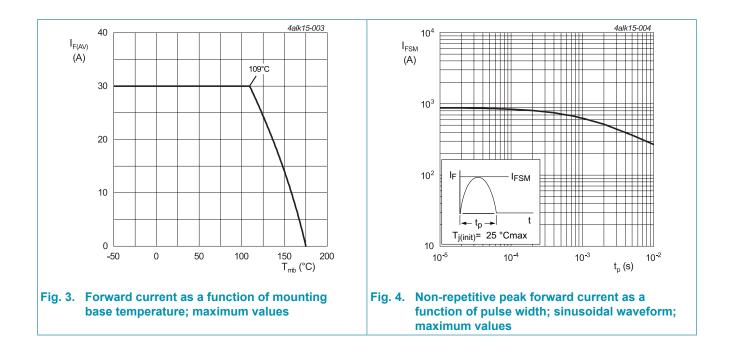


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

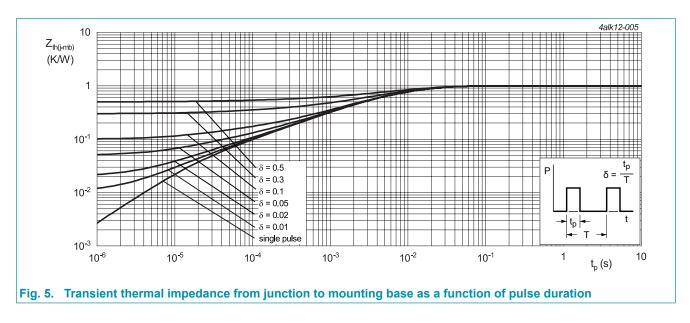
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BYC30M-650P Hyperfast power diode



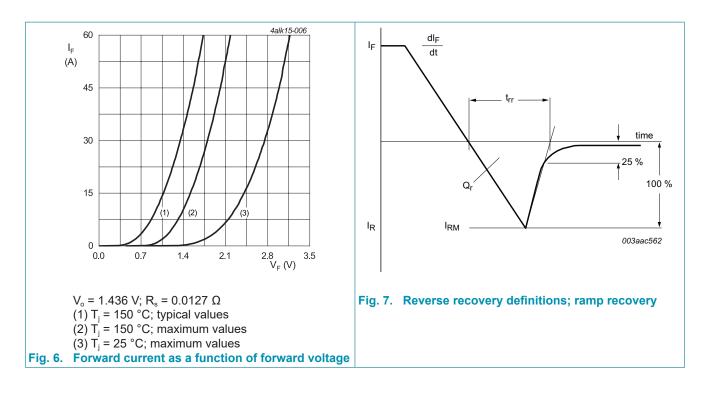
## 9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W



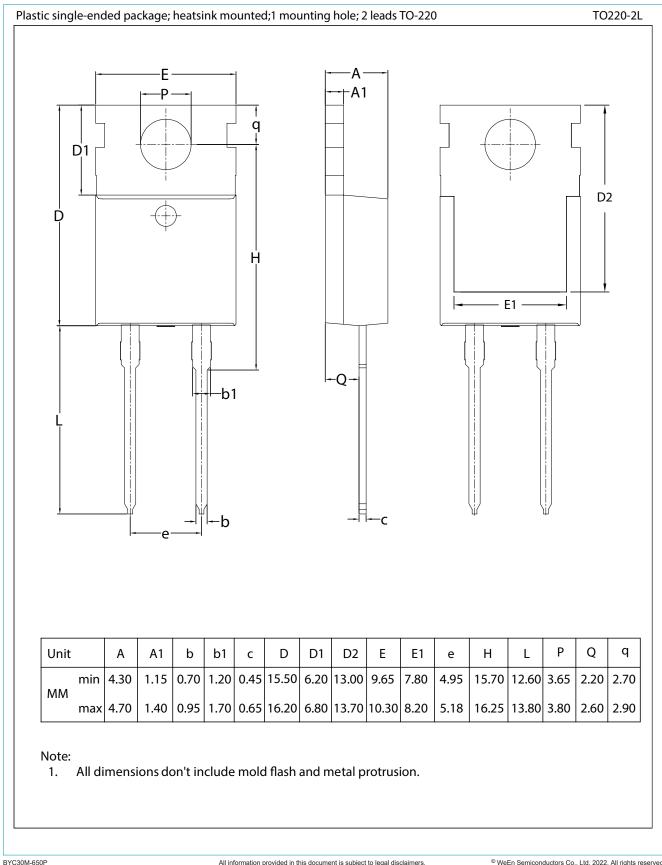
## **10. Characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
	aracteristics	I					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.05	2.75	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.38	1.80	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.6	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.25	1	mA
Dynamic	characteristics	1	,	1			
Q <sub>r</sub>	reverse charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	68	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 125 °C; <u>Fig. 7</u>		-	330	-	nC
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>		-	20	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; \text{ Fig. 7}$		-	38	-	ns
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	73	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	3.7	-	A
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>		-	9.1	-	А
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		30	-	-	mJ



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## **11. Package outline**



Product data sheet

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# BYC30M-650P

#### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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